

N-channel LFPAK 60 V, 8 mΩ standard level MOSFET 22 July 2015 Product data sheet

1. General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

3. Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

| Table 1. Qui | ck reference data | | | | | | |
|-------------------|----------------------------------|--|---|-----|-----|------|------|
| Symbol | Parameter | Conditions | N | Nin | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | - | 60 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u> | - | - | - | 76 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | - | - | 106 | W |
| Tj | junction temperature | | - | -55 | - | 175 | °C |
| Static charact | eristics | · | | | | - 1 | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 12 | - | - | - | 12.8 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 13 | - | _ | 5.6 | 8 | mΩ |
| Dynamic char | acteristics | · | | | | 1 | |
| Q _{GD} | gate-drain charge | V _{GS} = 10 V; I _D = 60 A; V _{DS} = 30 V; Fig. 15; Fig. 14 | - | - | 7.7 | - | nC |

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
|----------------------|---|--|--|-----|-----|-----|------|--|
| Q _{G(tot)} | total gate charge | V_{GS} = 10 V; I _D = 60 A; V _{DS} = 30 V; Fig. 14; Fig. 15 | | - | 39 | - | nC | |
| Avalanche rug | Avalanche ruggedness | | | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; I_{D} = 76 \; A; \\ V_{sup} \leq 60 \; V; \; R_{GS} = 50 \; \Omega; \; \text{unclamped} \end{array}$ | | - | - | 97 | mJ | |

5. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S | source | mb | D |
| 2 | S | source | | |
| 3 | S | source | | G-UFA |
| 4 | G | gate | ប្រុប្បូប | mbb076 S |
| mb | D | mounting base; connected to drain | 1 2 3 4 LFPAK56; Power- SO8 (SOT669) | |

6. Ordering information

| Table 3. Ordering in | formation | | | | |
|----------------------|-----------------------|--|---------|--|--|
| Type number | Package | | | | |
| | Name | Description | Version | | |
| PSMN8R5-60YS | LFPAK56; Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669 | | |

7. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| PSMN8R5-60YS | 8R560 |

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

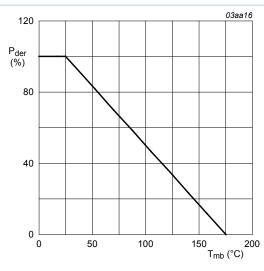
| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|----------------------|--|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 60 | V |
| V _{DGR} | drain-gate voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | 60 | V |

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| Symbol | Parameter | Conditions | Min | Мах | Unit |
|----------------------|--|---|-----|-----|------|
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | 106 | W |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | - | 54 | А |
| | | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | 76 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3 | - | 303 | А |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | - | 260 | °C |
| Source-dra | in diode | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 76 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$ | - | 303 | А |
| Avalanche | ruggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 76 A; V _{sup} ≤ 60 V; R _{GS} = 50 Ω; unclamped | - | 97 | mJ |

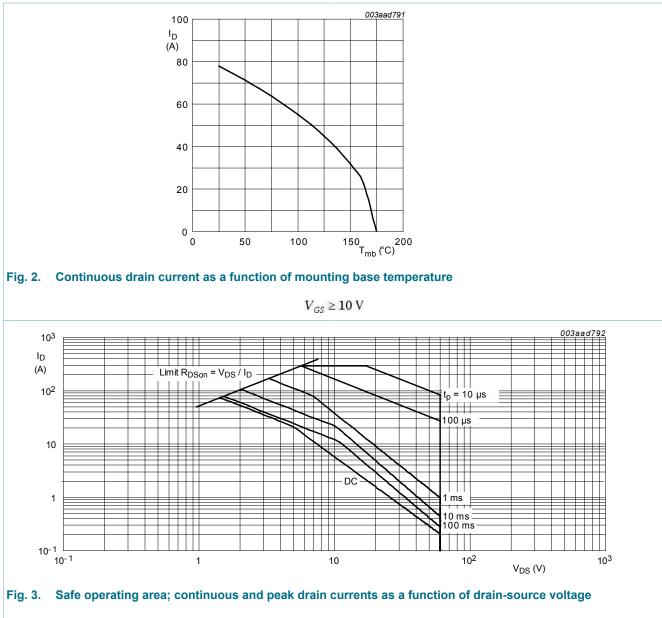




$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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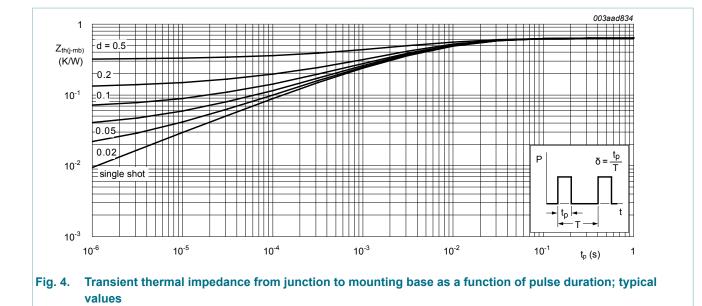


 $T_{mb} = 25 \text{ °C}; I_{DM}$ is a single pulse

9. Thermal characteristics

| Table 6. Th | ermal characteristics | | | | | |
|-----------------------|---|---------------|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 4</u> | - | 0.63 | 1.42 | K/W |

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10. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|----------------------------------|--|------|------|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 54 | - | - | V |
| | breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 60 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11 | 2 | 3 | 3.8 | V |
| V _{GSth} | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; <u>Fig. 11</u> | - | - | 4.3 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 11 | 0.95 | - | - | V |
| I _{DSS} | drain leakage current | V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.03 | 2 | μA |
| | | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 125 °C | - | - | 50 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| | | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; Fig. 12 | - | 12 | 18.4 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 12 | - | - | 12.8 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 13 | - | 5.6 | 8 | mΩ |
| R _G | gate resistance | f = 1 MHz | - | 0.61 | - | Ω |

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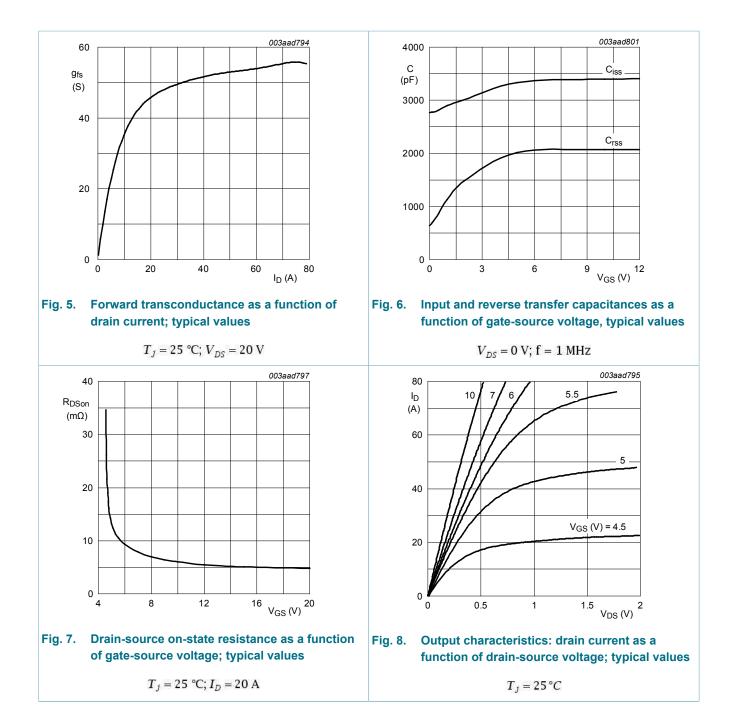
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|---------------------------------------|--|-----|------|-----|------|
| Dynamic ch | naracteristics | | I | | | |
| Q _{G(tot)} | total gate charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 14; Fig. 15 | - | 39 | - | nC |
| | | I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V | - | 33 | - | nC |
| Q _{GS} | gate-source charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 15; Fig. 14 | - | 13.3 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 14 | - | 7 | - | nC |
| $Q_{GS(\text{th-pl})}$ | post-threshold gate- source charge | | - | 6.2 | - | nC |
| Q _{GD} | gate-drain charge | I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 15; Fig. 14 | - | 7.7 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | V _{DS} = 30 V; <u>Fig. 14</u> ; <u>Fig. 15</u> | - | 5.2 | - | V |
| C _{iss} | input capacitance | V_{DS} = 30 V; V_{GS} = 0 V; f = 1 MHz; | - | 2370 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 16</u> | - | 307 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 172 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 30 V; R _L = 0.5 Ω; V _{GS} = 10 V; | - | 18.4 | - | ns |
| t _r | rise time | $R_{G(ext)} = 4.7 \Omega$ | - | 13.7 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 32.4 | - | ns |
| t _f | fall time | 1 | - | 9.2 | - | ns |
| Source-dra | in diode | | I | | | |
| V _{SD} | source-drain voltage | I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u> | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | I_{S} = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; | - | 43.3 | - | ns |
| Qr | recovered charge | V _{DS} = 30 V | - | 61.4 | - | nC |

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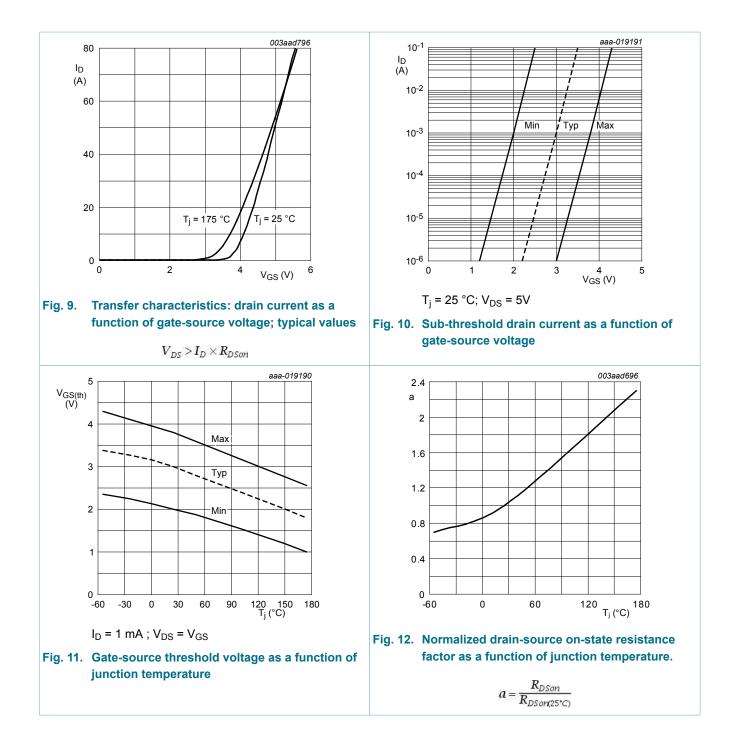
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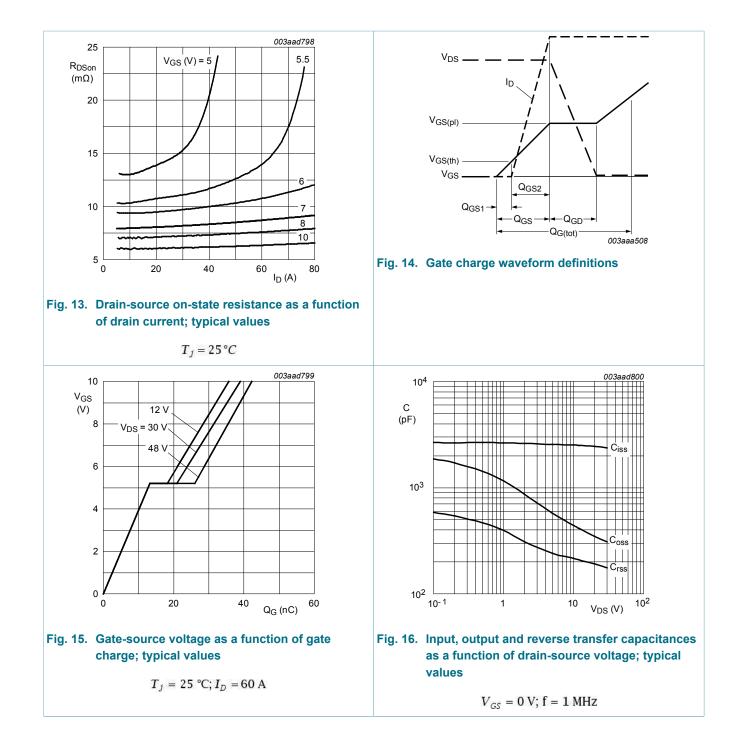
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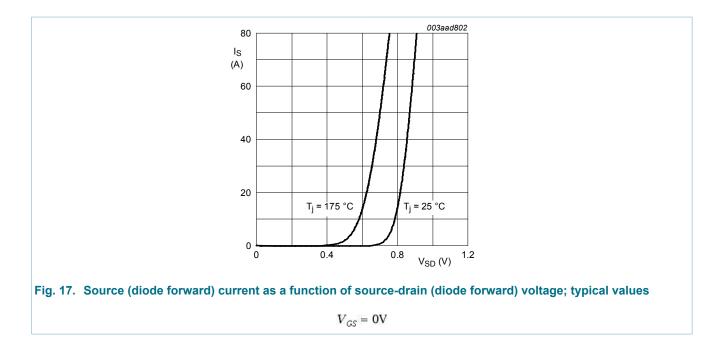
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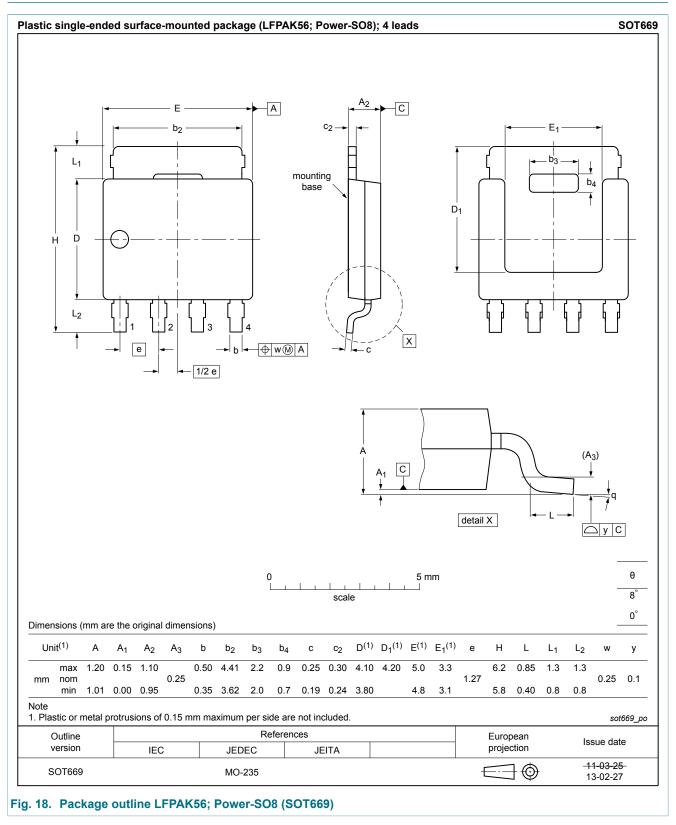
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11. Package outline



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|--------------------------------------|-------------------------------|---|
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